

TVS Diode

Transient Voltage Suppressor Diodes

ESD3V3S1B Series

Ultra Low Clamping Bi-directional ESD / Transient Protection Diode

ESD3V3S1B-02LRH
ESD3V3S1B-02LS

Data Sheet

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Final

Industrial and Multi-Market

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Revision History

Page or Item	Subjects (major changes since previous revision)
Revision 1.1, 2011-11-28	
Revision 1.1; 2011-11-28	Features 1.1; Table 3-1; Table 3-3; Table 3-4

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1 Ultra Low Clamping Bi-directional ESD / Transient Protection Diode

1.1 Features

- ESD / transient protection of signal lines in low voltage applications according to:
 - IEC61000-4-2 (ESD): ± 30 kV (contact)
 - IEC61000-4-4 (EFT): 40 A (5/50 ns)
 - IEC61000-4-5 (surge): 8 A (8/20 μ s)
- Bi-directional, symmetrical working voltage up to $V_{RWM} = \pm 3.3$ V
- Ultra low clamping voltage $V_{CL} = 7$ V typ. @ $I_{PP} = 16$ A (TLP)
- Ultra low dynamic resistance $R_{DYN} = 0.13 \Omega$ typ.
- Smallest form factor: $0.62 \times 0.32 \times 0.31$ mm³
- Pb-free (RoHS compliant) and halogen free package



1.2 Application Examples

- Audio Line, Speaker, Headset, Microphone Protection
- Human Interface Devices (Keyboard, Touchpad, Buttons)

2 Product Description

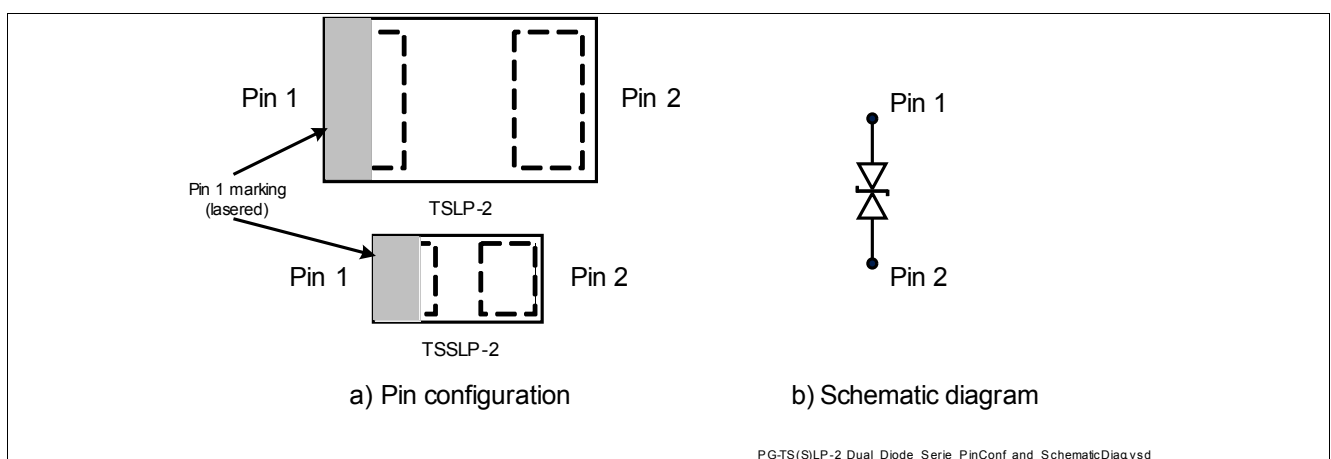


Figure 2-1 Pin Configuration and Schematic Diagram

Table 2-1 Ordering Information

Type	Package	Configuration	Marking code
ESD3V3S1B-02LRH	PG-TSLP-2-17	1 line, bi-directional	Y
ESD3V3S1B-02LS	PG-TSSLP-2-1	1 line, bi-directional	Y

3 Characteristics

Table 3-1 Maximum Ratings at $T_A = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
ESD contact discharge ¹⁾	V_{ESD}	–	–	30	kV
Peak pulse current ($t_p = 8/20\text{ }\mu\text{s}$) ²⁾	I_{PP}	–	–	8	A
Operating temperature range	T_{OP}	-40	–	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-65	–	150	$^\circ\text{C}$

1) V_{ESD} according to IEC61000-4-2

2) I_{PP} according to IEC61000-4-5

3.1 Electrical Characteristics at $T_A = 25\text{ }^\circ\text{C}$, unless otherwise specified

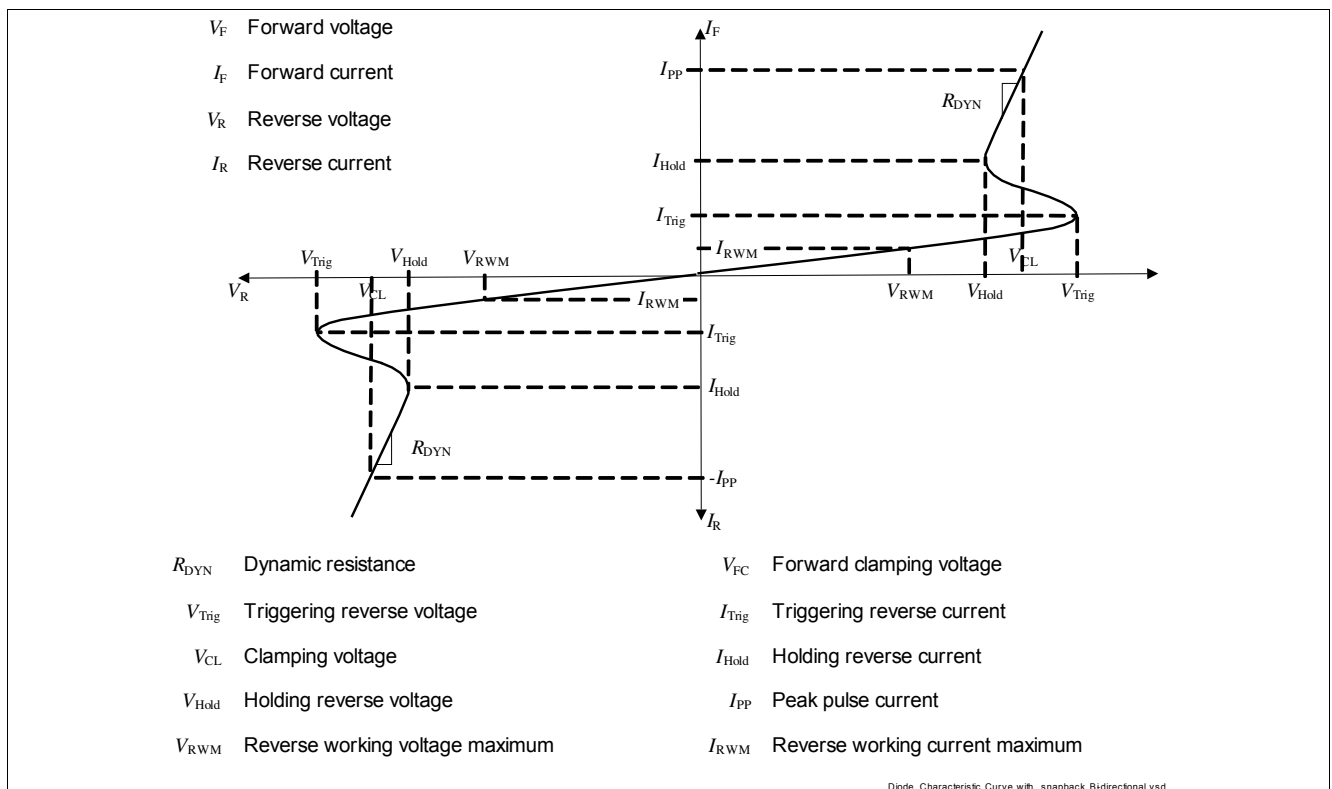


Figure 3-1 Definitions of electrical characteristics

Table 3-2 DC Characteristics at $T_A = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Reverse working voltage	V_{RWM}	-3.3	–	3.3	V	
Reverse current	I_R	–	–	50	nA	$V_R = 3.3\text{ V}$

Table 3-3 RF Characteristics at $T_A = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Line capacitance	C_L	–	14	20	pF	$V_R = 0\text{ V}, f = 1\text{ MHz}$

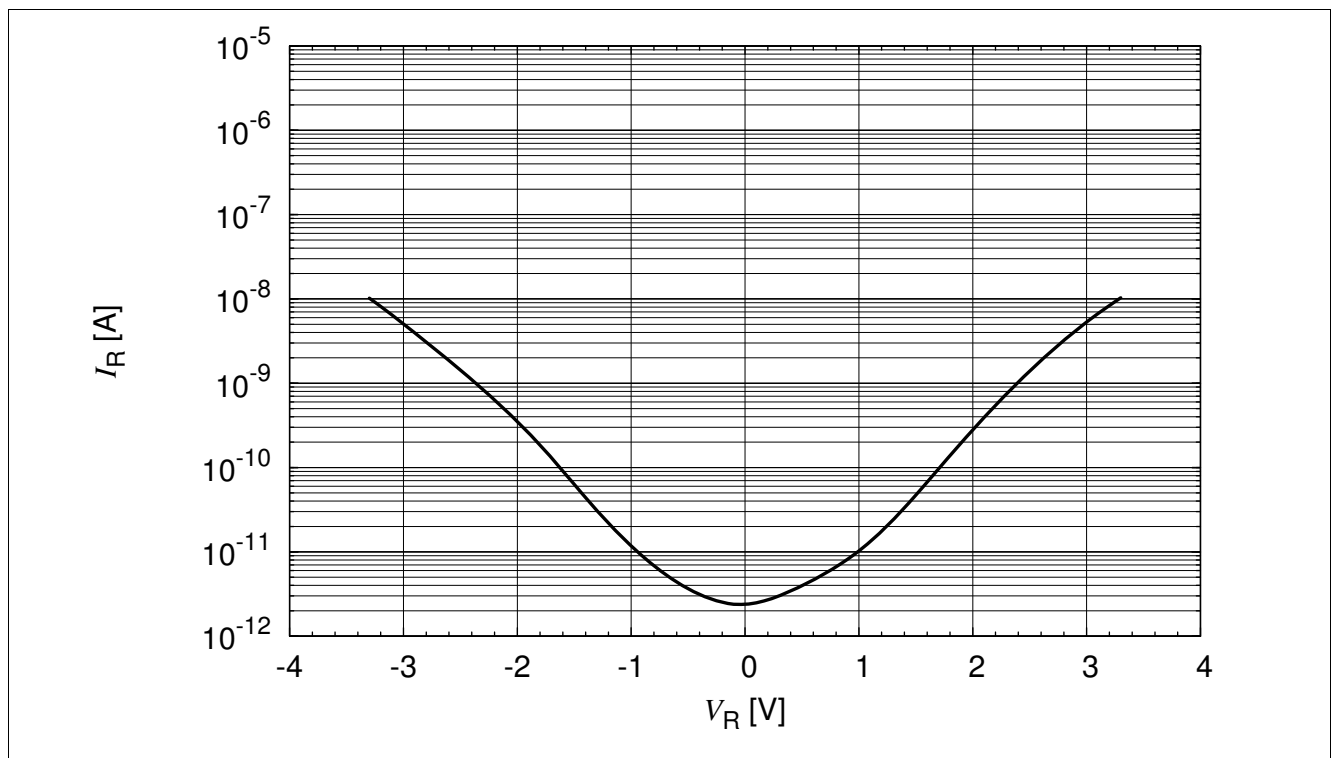
Table 3-4 ESD Characteristics at $T_A = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Clamping voltage ¹⁾	V_{CL}	–	7	–	V	$I_{PP} = 16\text{ A}, t_p = 100\text{ ns}$
		–	9	–	V	$I_{PP} = 30\text{ A}, t_p = 100\text{ ns}$
Clamping voltage ²⁾	V_{CL}	–	4.5	–	V	$I_{PP} = 1\text{ A}, t_p = 8/20\text{ }\mu\text{s}$
		–	6.8	–	V	$I_{PP} = 8\text{ A}, t_p = 8/20\text{ }\mu\text{s}$
Dynamic resistance ¹⁾	R_{DYN}	–	0.13	–	Ω	

1) Please refer to Application Note AN210 [1]. TLP parameter: $Z_0 = 50\text{ }\Omega$, $t_p = 100\text{ ns}$, $t_r = 300\text{ ps}$, averaging window: $t_1 = 30\text{ ns}$ to $t_2 = 60\text{ ns}$, extraction of dynamic resistance using least squares fit of TLP characteristics between $I_{PP1} = 10\text{ A}$ and $I_{PP2} = 40\text{ A}$.

2) I_{PP} according to IEC61000-4-5

3.2 Typical Characteristics at $T_A = 25\text{ }^\circ\text{C}$, unless otherwise specified


Figure 3-2 Reverse current: $I_R = f(V_R)$

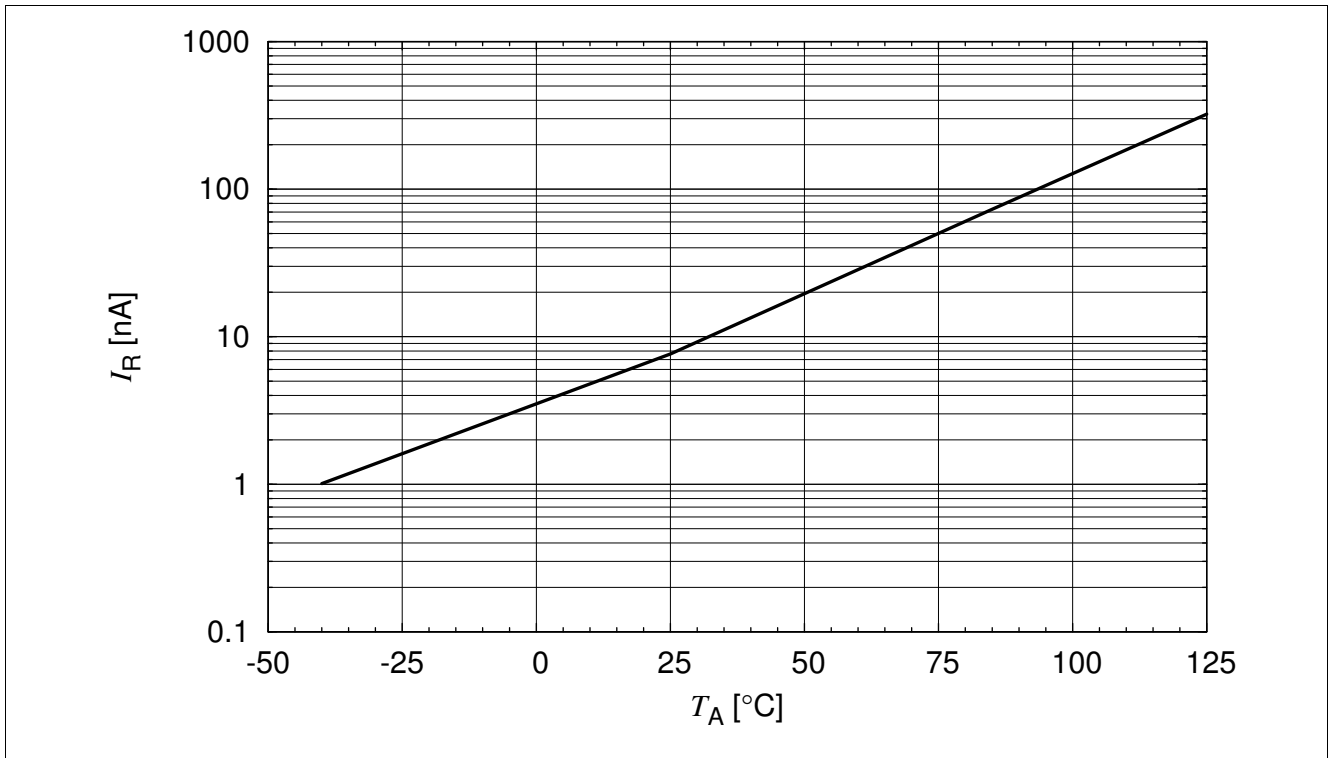


Figure 3-3 Reverse current: $I_R = f(T_A)$, $V_R = 3.3 V$

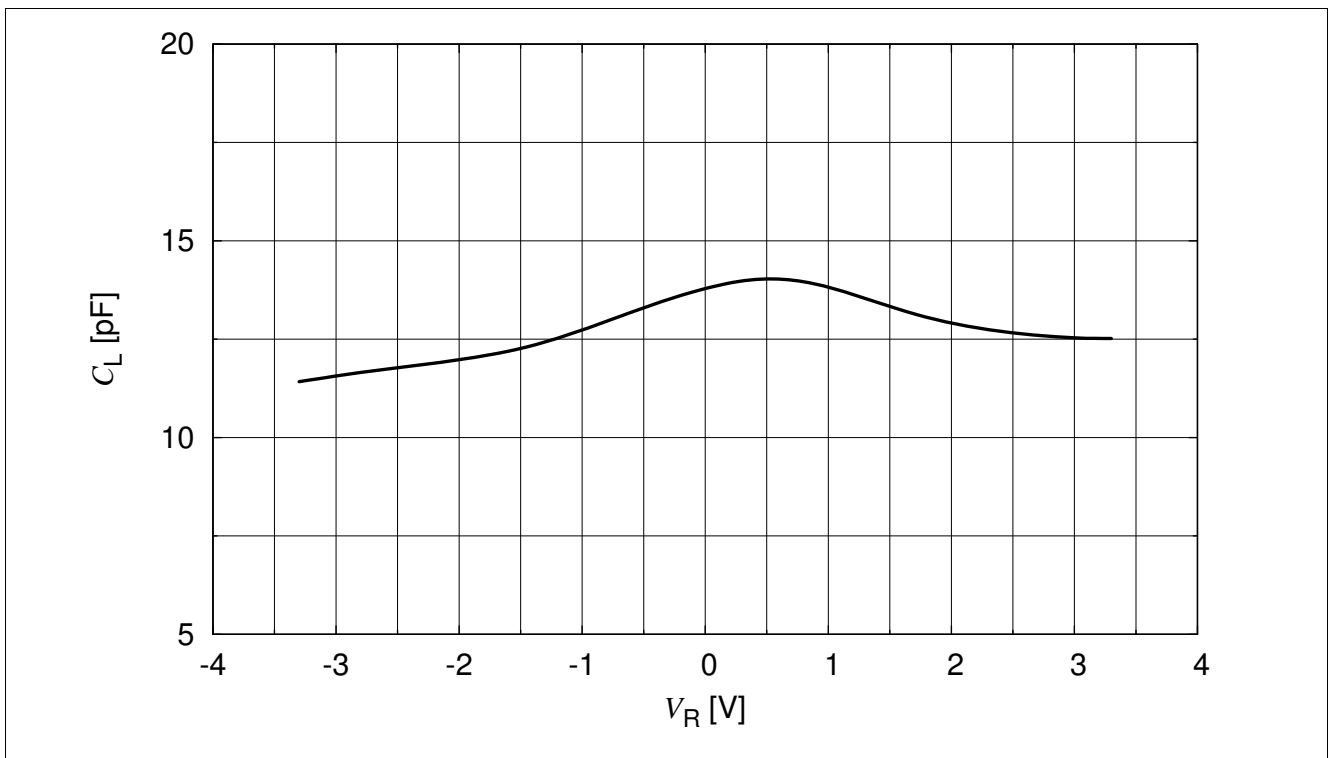


Figure 3-4 Line capacitance: $C_L = f(V_R)$, $f = 1 MHz$

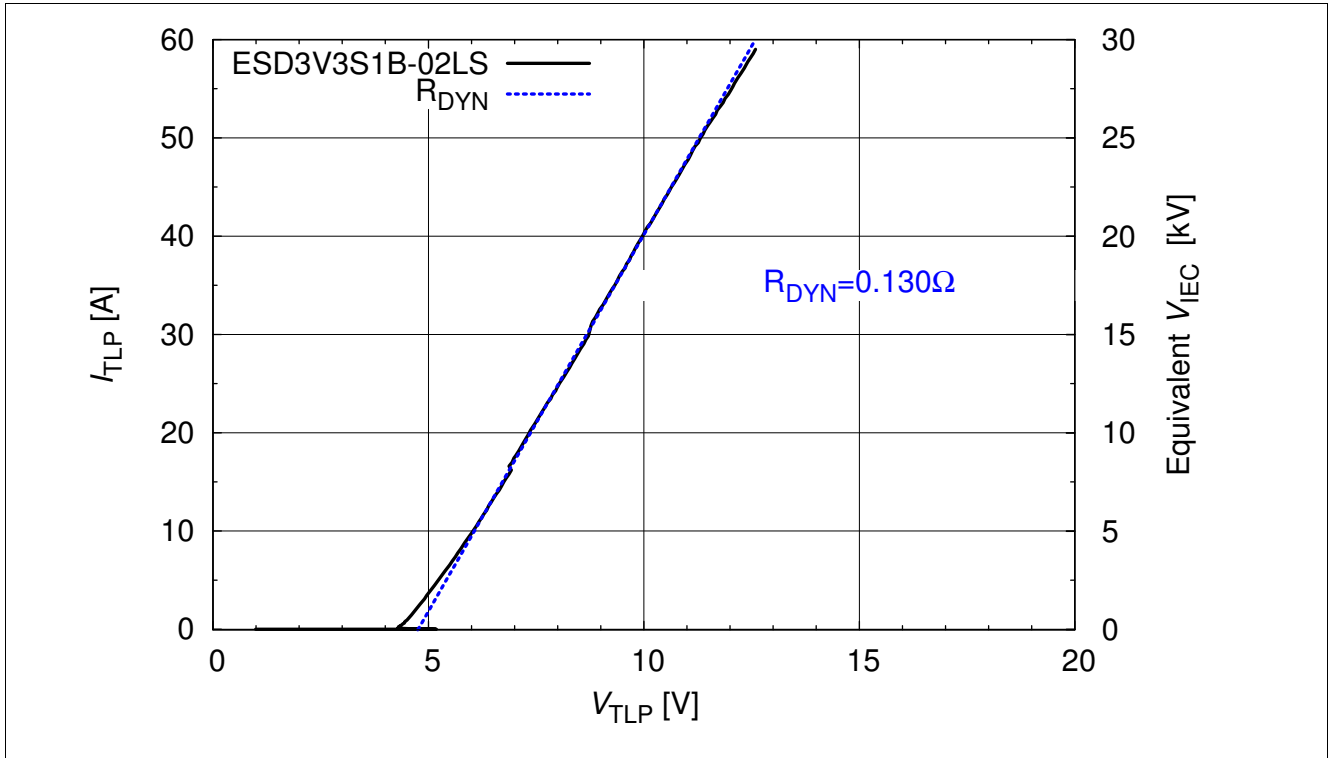


Figure 3-5 Clamping voltage (TLP): $I_{TLP} = f(V_{TLP})$, from pin 1 to pin 2 [1]

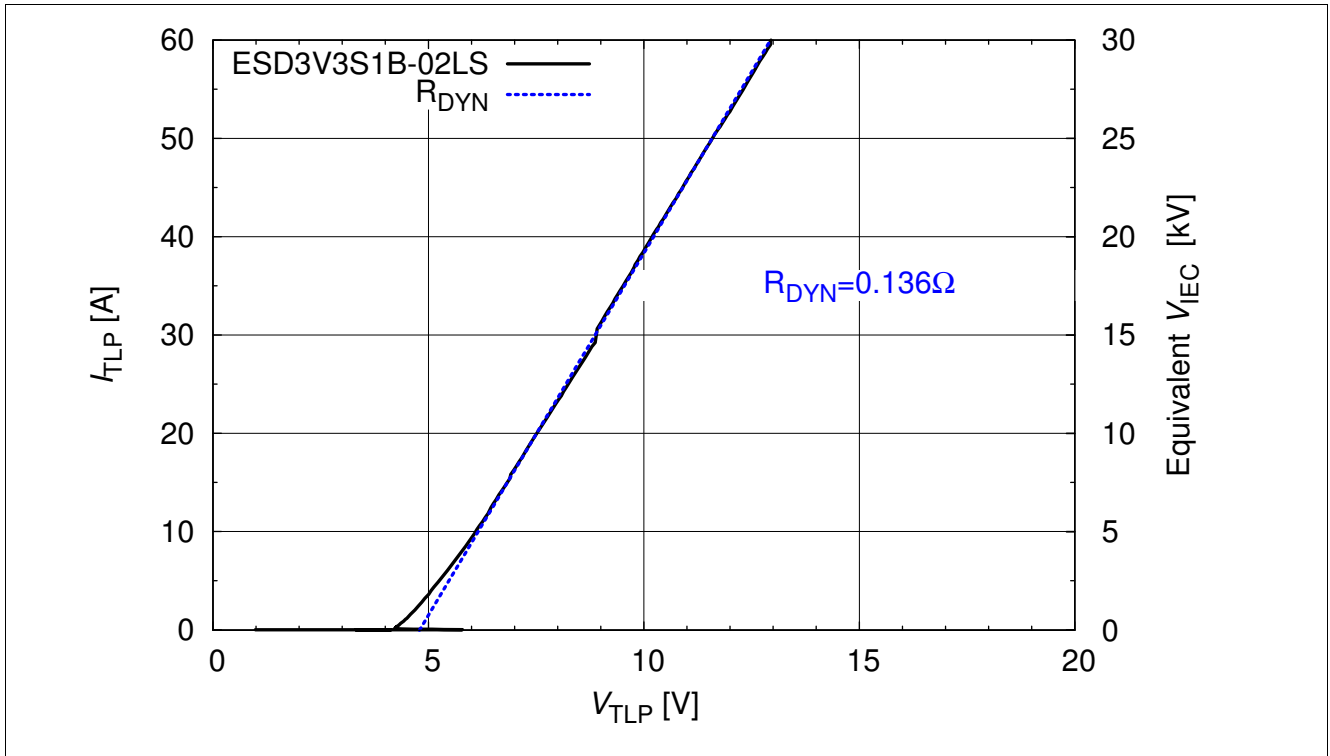


Figure 3-6 Clamping voltage (TLP): $I_{TLP} = f(V_{TLP})$, from pin 2 to pin 1 [1]

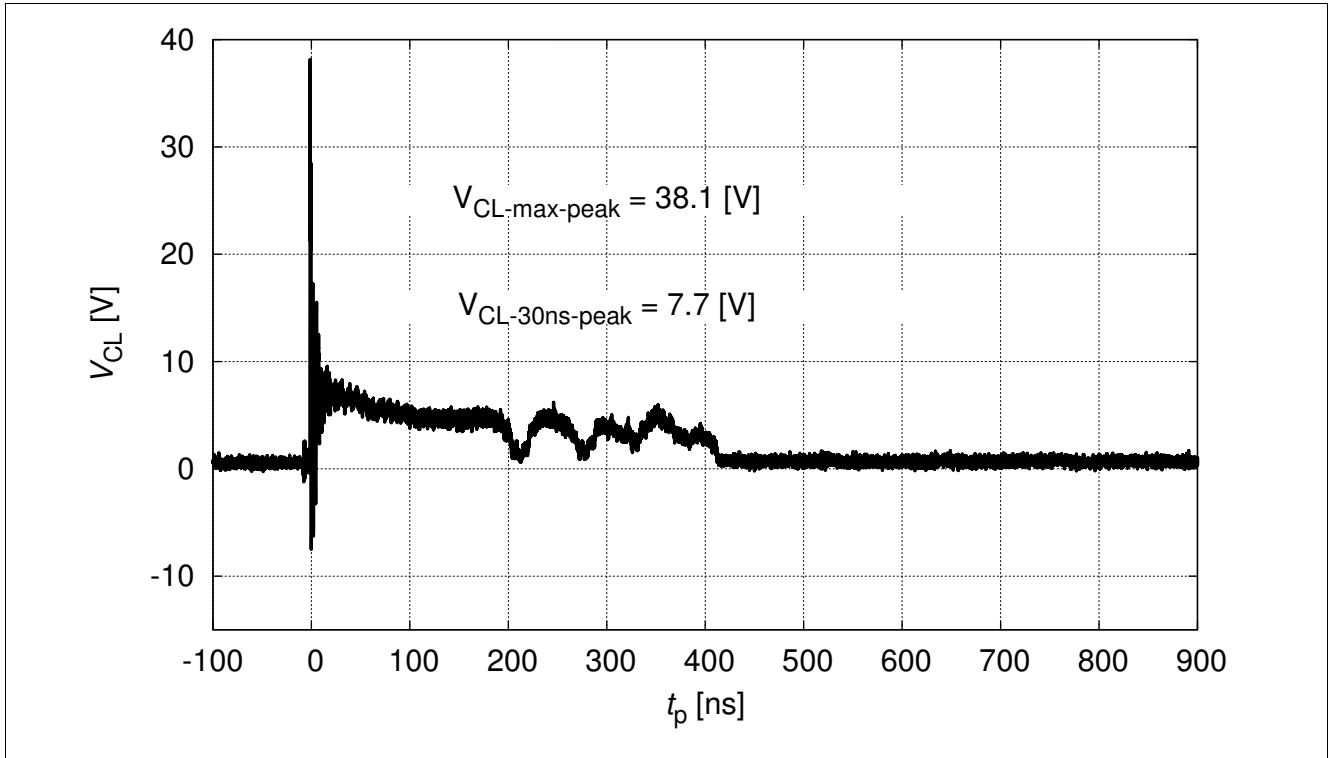


Figure 3-7 IEC61000-4-2 : $V_{CL} = f(t)$, 8 kV positive pulse from pin 1 to pin 2

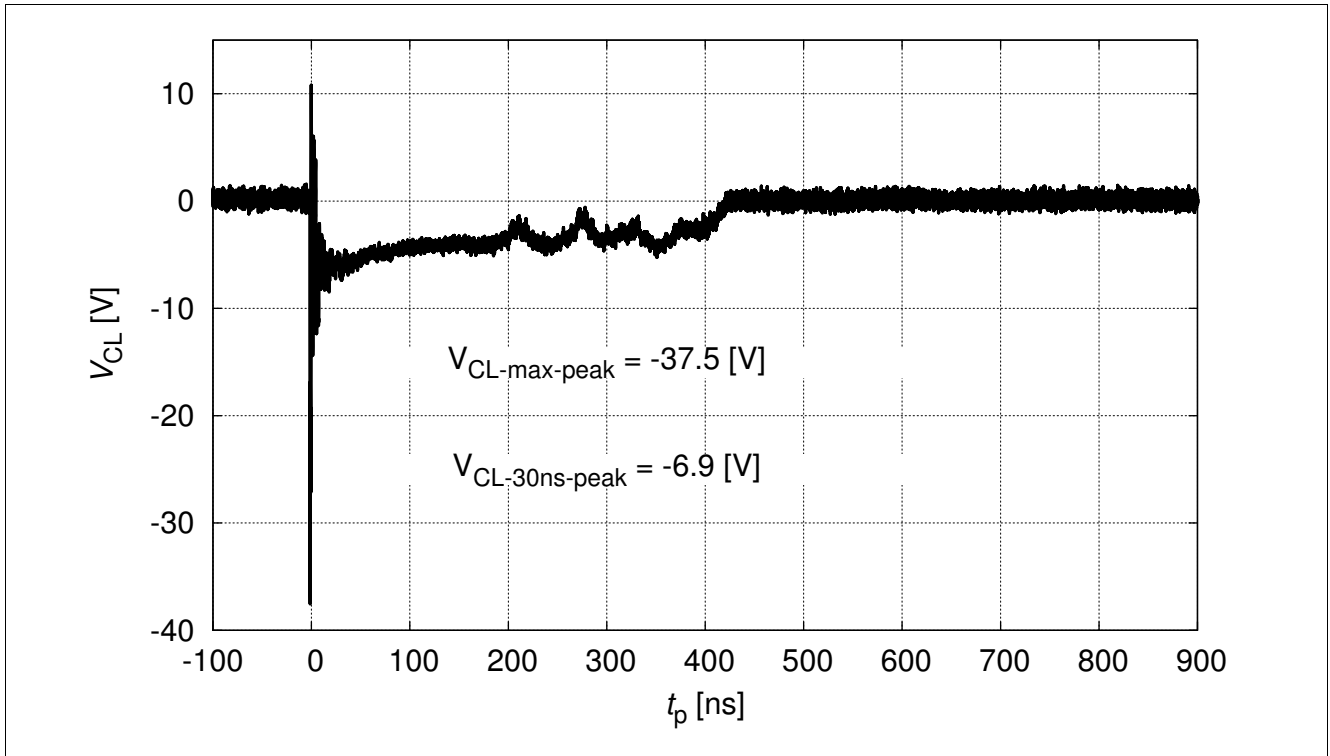


Figure 3-8 IEC61000-4-2 : $V_{CL} = f(t)$, 8 kV negative pulse from pin 1 to pin 2

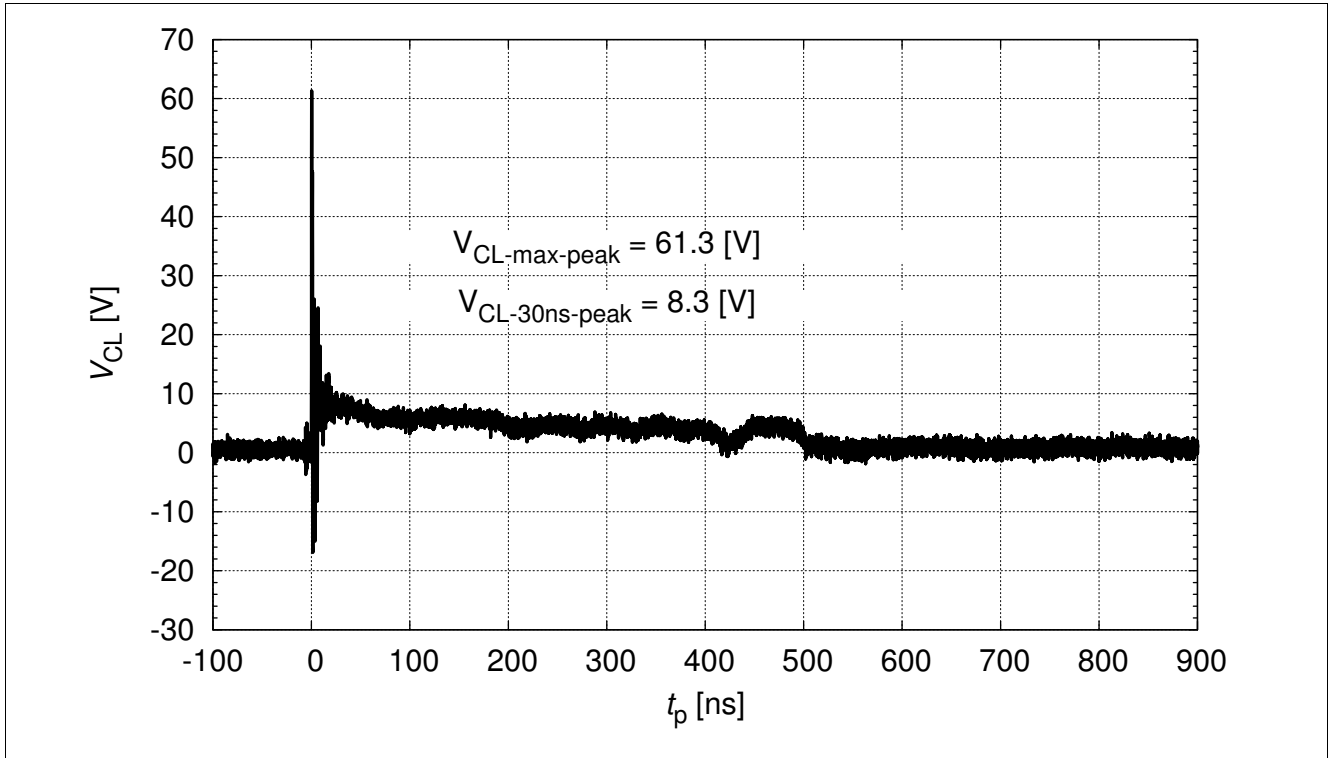


Figure 3-9 IEC61000-4-2 : $V_{CL} = f(t)$, 15 kV positive pulse from pin 1 to pin 2

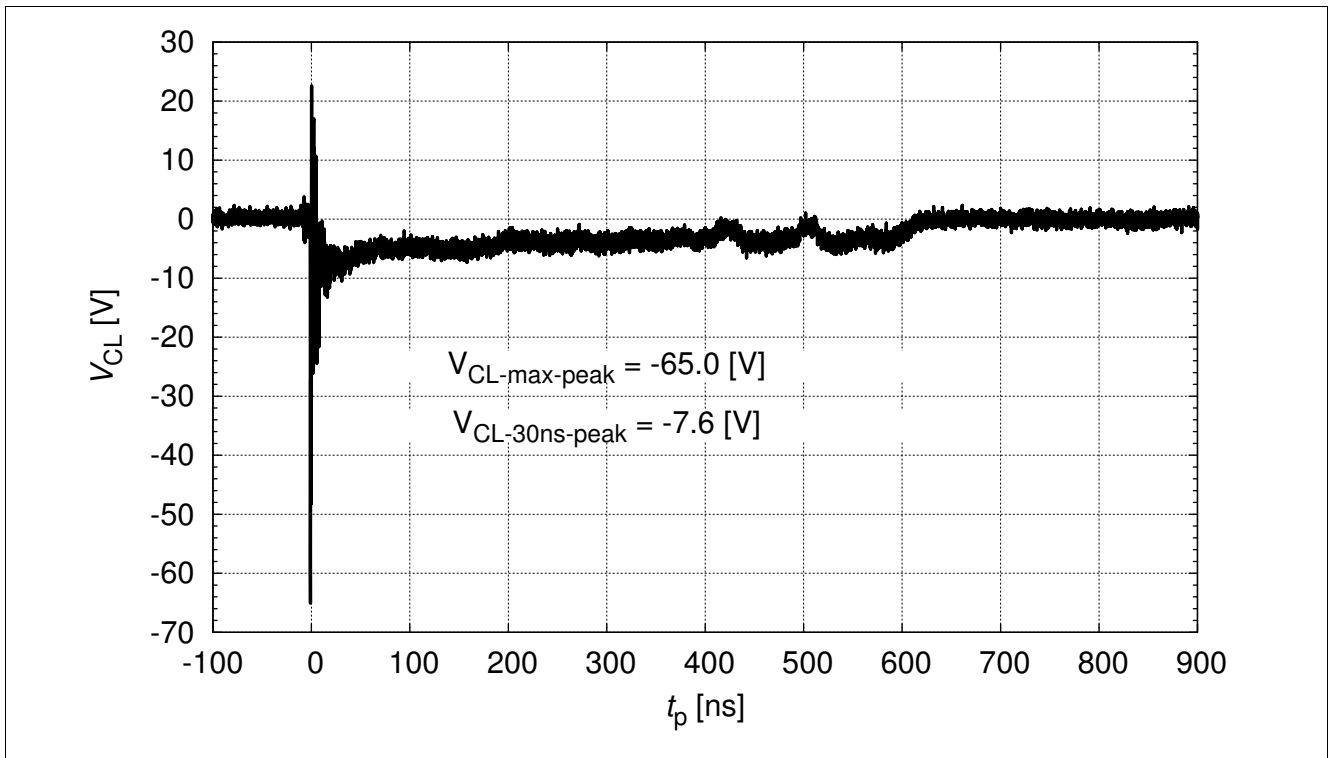


Figure 3-10 IEC61000-4-2 : $V_{CL} = f(t)$, 15 kV negative pulse from pin 1 to pin 2

4 Application Information

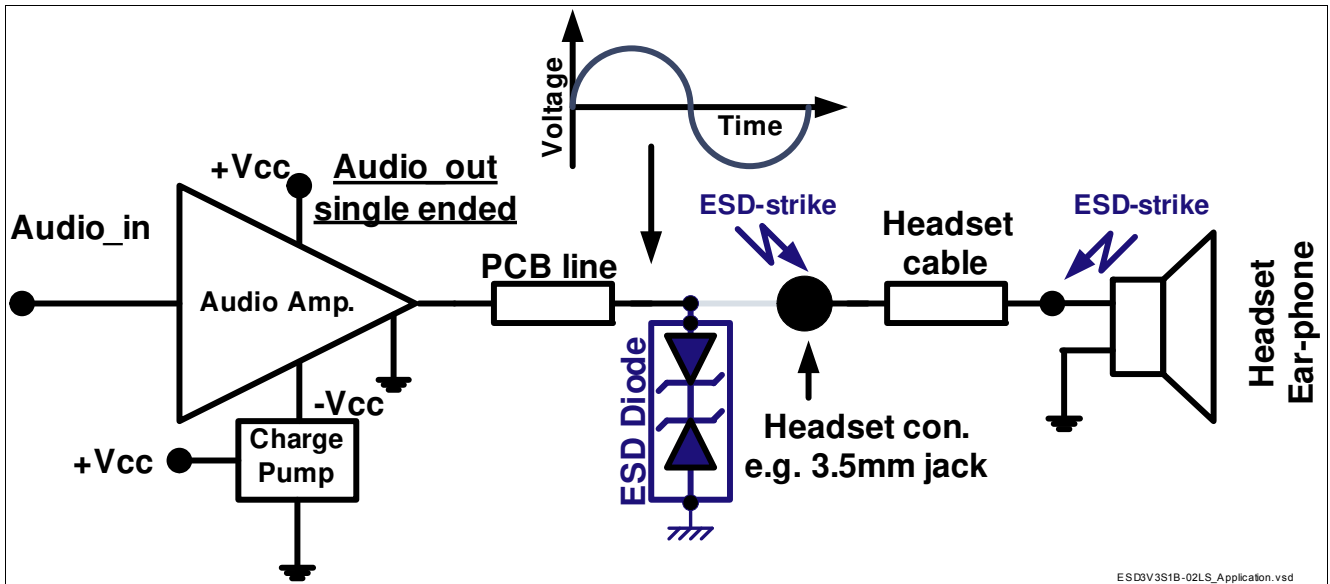


Figure 4-1 Single line, bi-directional ESD / Transient protection

5 Ordering Information Scheme (Examples)

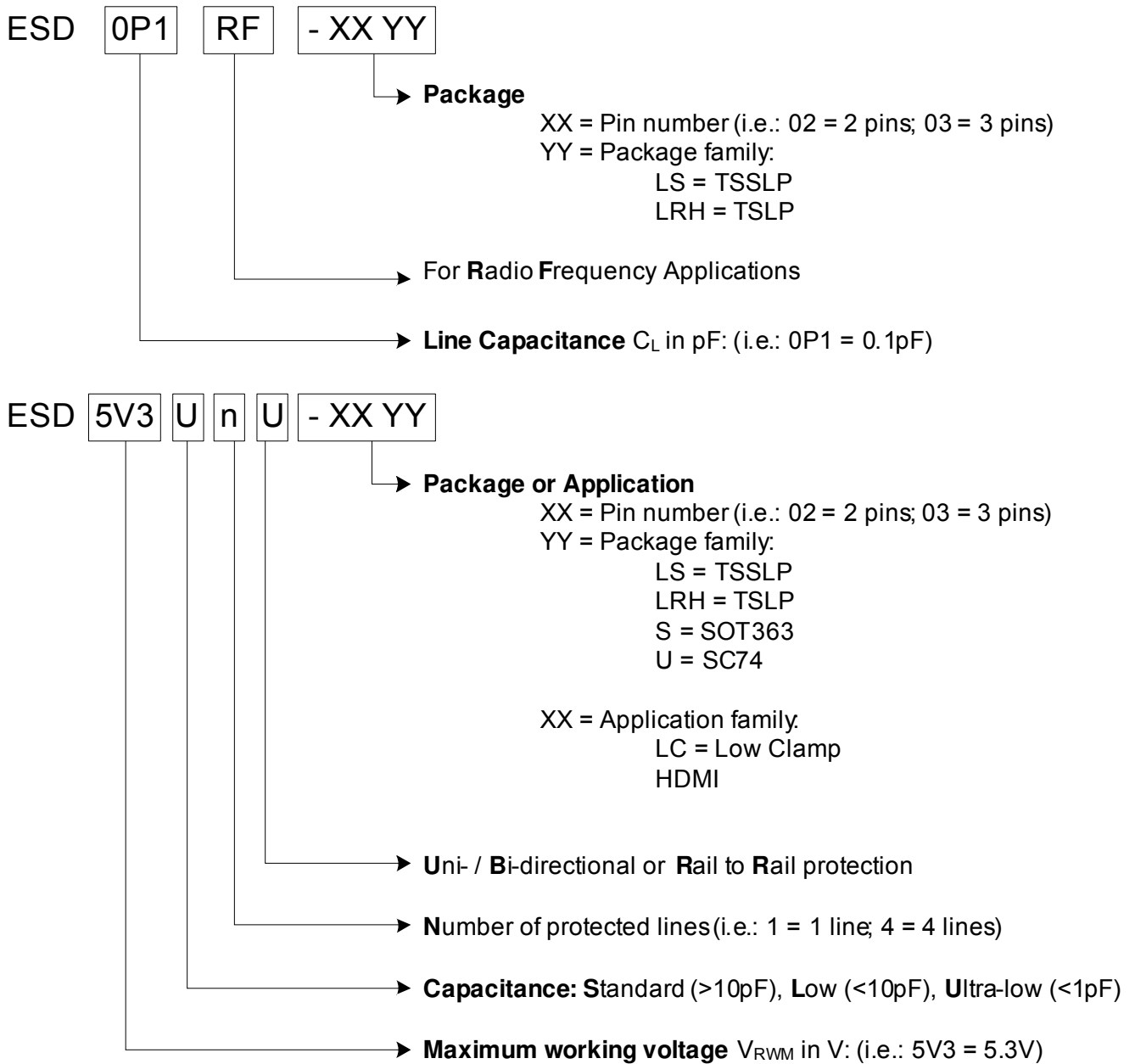


Figure 5-1 Ordering information scheme

6 Package Information

6.1 PG-TSLP-2-17 (mm) [2]

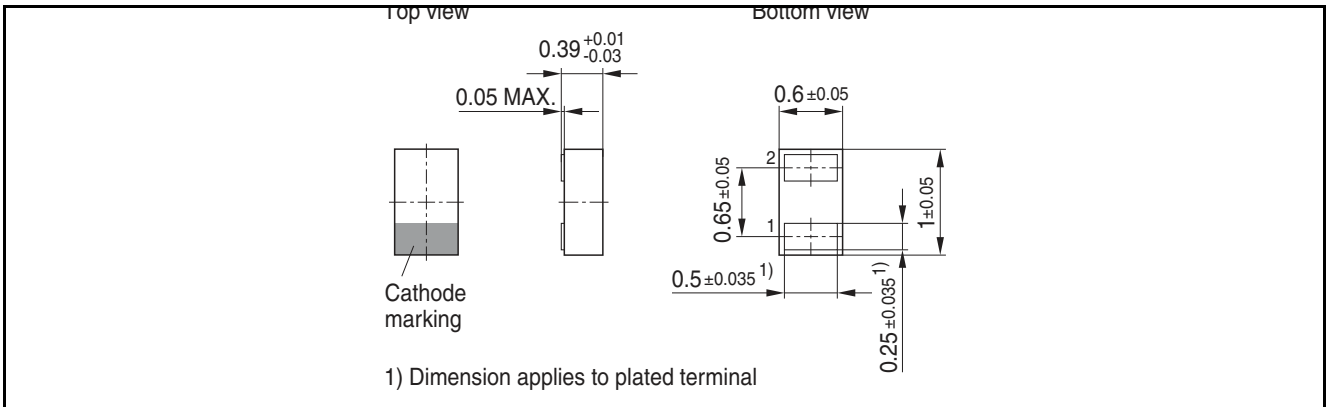


Figure 6-1 PG-TSLP-2-17: Package overview

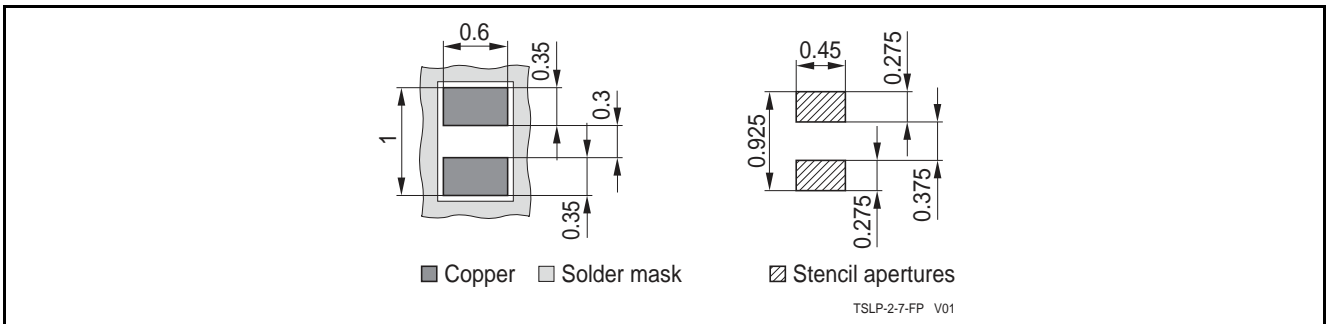


Figure 6-2 PG-TSLP-2-17: Footprint

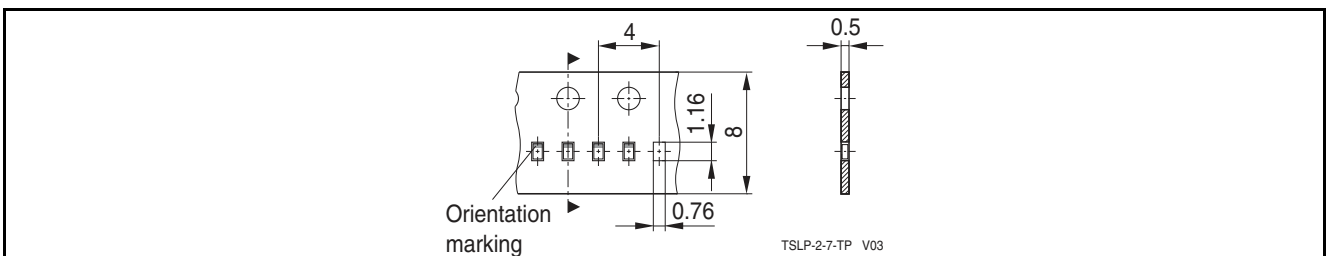


Figure 6-3 PG-TSLP-2-17: Packing

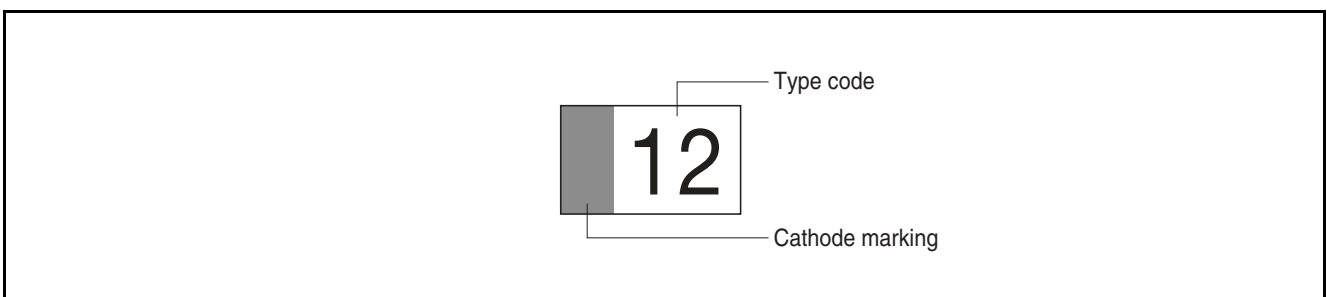


Figure 6-4 PG-TSLP-2-17: Marking (example)

6.2 PG-TSSLP-2-1 (mm) [2]

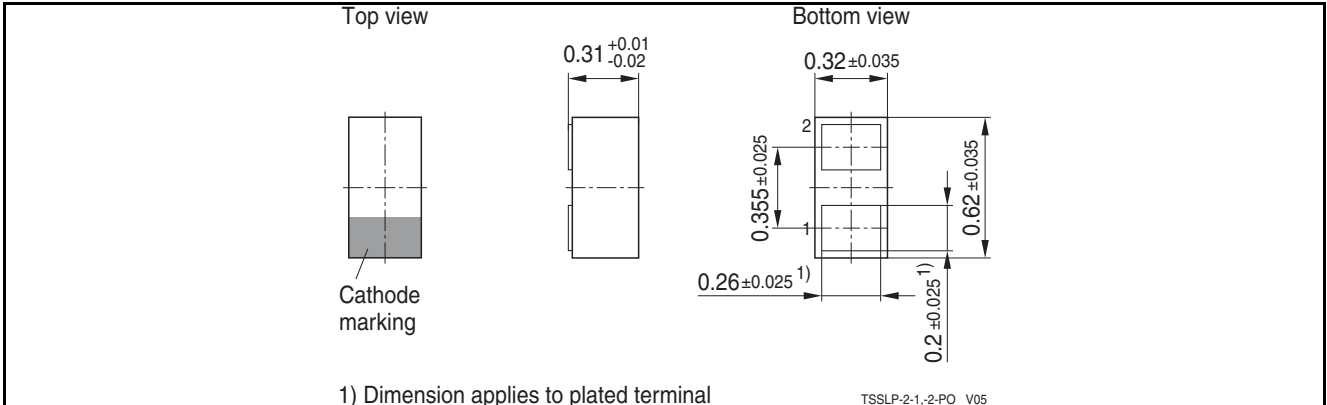


Figure 6-5 PG-TSSLP-2-1: Package overview

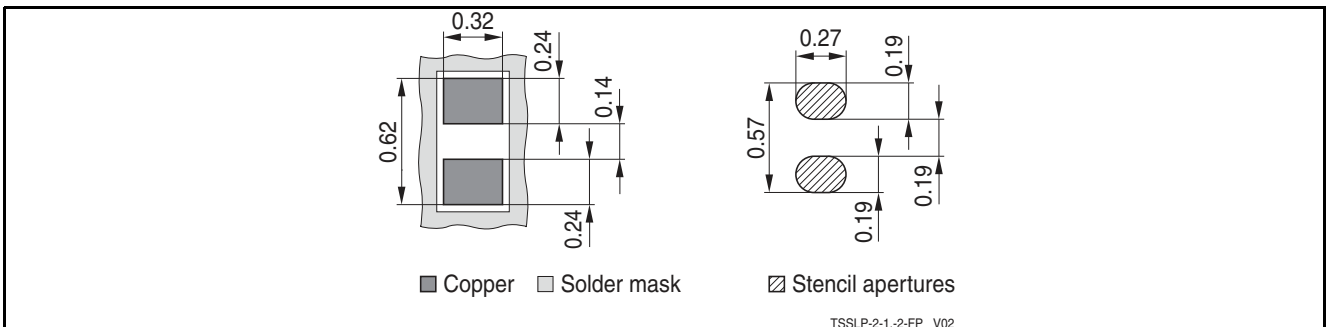


Figure 6-6 PG-TSSLP-2-1: Footprint

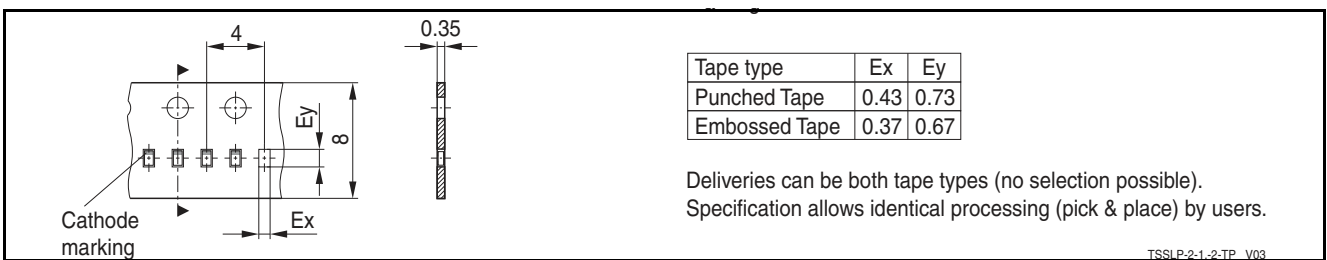


Figure 6-7 PG-TSSLP-2-1: Packing

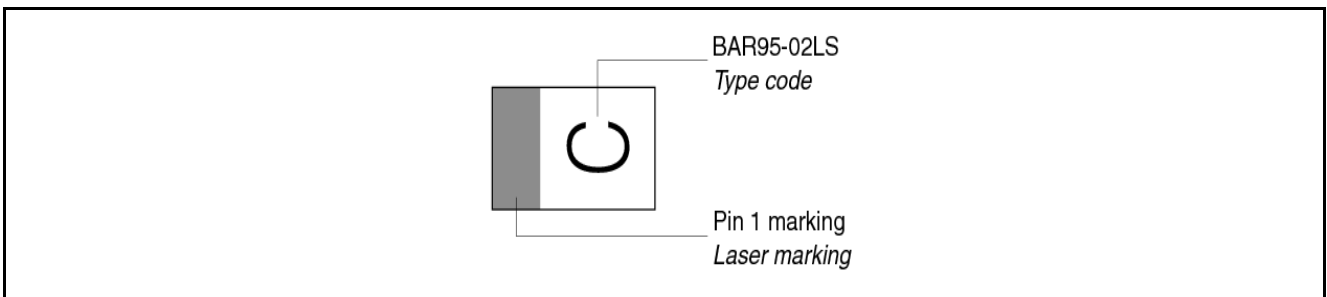


Figure 6-8 PG-TSSLP-2-1: Marking (example)

References

- [1] Infineon AG - **Application Note AN210: Effective ESD Protection design at System Level Using VF-TLP Characterization Methodology**
- [2] Infineon AG - Recommendations for PCB Assembly of Infineon TSLP and TSSLP Packages

Terminology

C_L	Line capacitance
EFT	Electrical Fast Transient
ESD	Electrostatic Discharge
I_{PP}	Peak pulse current
I_R	Reverse current
LCD	Liquid Crystal Display
P_{PK}	Peak pulse power
R_{DYN}	Dynamic resistance
RoHs	Restriction of Hazardous Substance directive
T_A	Ambient temperature
T_{OP}	Operation temperature
t_p	Pulse duration
T_{stg}	Storage temperature
V_{BR}	Breakdown voltage
V_{CL}	Reverse clamping voltage
V_{ESD}	Electrostatic discharge voltage
V_R	Reverse voltage
V_{RWM}	Reverse working voltage maximum

Predefined Names

Name	Initial Cross-Reference
X-GOLD	X-GOLD
XMM	XMM

Definition of “Predefined Names”

Frequently used expressions, such as component names, file names, tools releases, version numbers, proprietary variables and software links, can be used in a similar way as user variables. However, they must be listed in a special table and **not** in the standard file “Variables”.

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2. New definitions must be inserted in a new row. Never change existing definitions, as they might be used in other documents.
3. This file does not need to be included in your book, but it must be in the fm sub-folder of your document.
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